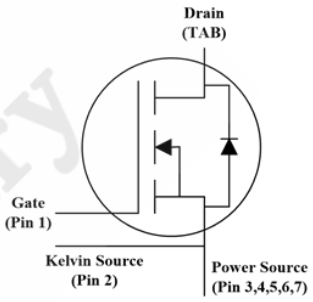
SiC MOS P3M12080G7

N-Channel Enhancement Mode

Features

- Qualified to AEC-Q101
- High Blocking Voltage with Low On-Resistance
- High-Frequency Operation
- Ultra-Small Q_{gd}
- 100% UIS tested



Benefits

- Improve System Efficiency
- Increase Power Density
- Reduce Heat Sink Requirements
- Reduction of System Cost

TO-263-7

Drain	TAB
Gate	1
Kelvin Source	2
Power Source	3~7

Applications

- Solar Inverters
- EV Battery Chargers
- High Voltage DC/DC Converters
- Switch Mode Power Supplies

RoHS

Halogen

Order Information

Part Number	Package	Marking
P3M12080G7	TO-263-7	P3M12080G7

PNJ Preliminary

Contents

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.

1. Maximum Ratings

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmax}	1200	V	V_{GS} = 0V I_D = 100μA
Gate - Source Voltage (dynamic)	V_{GSmax}	-8 / +21	V	AC (f >1Hz)
Gate - Source Voltage(static) turn-on gate voltage turn-off gate voltage	 $V_{GS,on}$ $V_{GS,off}$	 +15 / +18 -3	V	Static
Continuous Drain Current	I_D	32	A	V_{GS} = 15V T_C = 25℃
		23		V_{GS} = 15V T_C = 100℃
Power Dissipation	P_D	136	W	
Operating Junction	T_J	-55 To +175	˚C	
Storage Temperature	T_{stg}	-55 To +175	˚C	
Solder Temperature	T_L	260	˚C	

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.

2. Electrical Characteristics

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200	/	/	V	V_{GS}= 0V I_D= 100μA
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.4	/	V	(tested after 30ms pulse at V_{GS}=15V) V_{DS}= V_{GS} I_D= 5mA T_J = 25℃
		/	1.6	/	V	V_{DS}= V_{GS} I_D= 5mA T_J = 175℃
Zero Gate Voltage Drain Current	I_{DSS}	/	1.8	100	μA	V_{GS}=0V V_{DS}=1200V
Gate-Source Leakage Current	I_{GSS}	/	20	250	nA	V_{GS}= 15V V_{DS}= 0V
Drain-Source On-State Resistance	$R_{DS(on)}$	/	80	104	mΩ	V_{GS}= 15V I_D= 20A T_J = 25℃
		/	104	/		V_{GS}= 15V I_D= 20A T_J = 175℃
		/	66	/		V_{GS}= 18V I_D= 20A T_J = 25℃

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Transconductance	g_{fs}	/	10	/	S	V_{DS}= 20V I_{DS}= 20A T_J = 25℃
		/	9.6	/		V_{DS}= 20V I_{DS}= 20A T_J= 175℃
Input Capacitance	C_{iss}	/	2032	/	pF	V_{GS}= 0V V_{DS}= 800V f= 1MHz V_{AC}= 25mV
Output Capacitance	C_{oss}	/	73.6	/		
Reverse Transfer Capacitance	C_{rss}	/	6	/		
Coss Stored Energy	E_{oss}	/	52.9	/	μJ	
Internal Gate Resistance	$R_{G(int)}$	/	3.5	/	Ω	f= 1MHz V_{AC}= 25mV
Gate to Source Charge	Q_{gs}	/	22.2	/	nC	V_{DS}= 800V I_{DS}= 20A V_{GS}= -3 to 15V I_G= 20mA
Gate to Drain Charge	Q_{gd}	/	12.3	/		
Total Gate Charge	Q_g	/	54.6	/		

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.

3. Reverse Diode Characteristics

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Diode Forward Voltage	V_{SD}	5.2	/	V	V_{GS}= -3V I_{SD}= 10A T_J= 25℃
		4.8	/	V	V_{GS}= -3V I_{SD}= 10A T_J= 175℃
Continuous Diode Forward Current	I_S	31	/	A	V_{GS}= -3V

4. Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.1	℃/W

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.

5. Typical Performance

At T_J= 25℃, unless specified otherwise

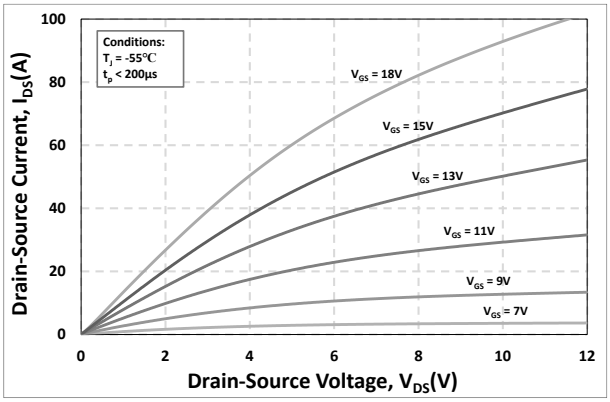


Figure 1. Output Characteristics T_J = -55℃

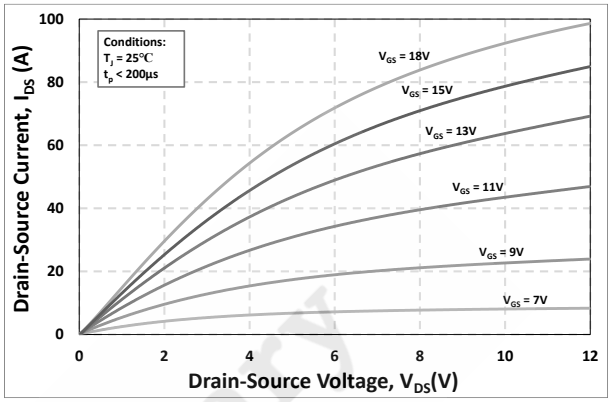


Figure 2. Output Characteristics T_J = 25℃

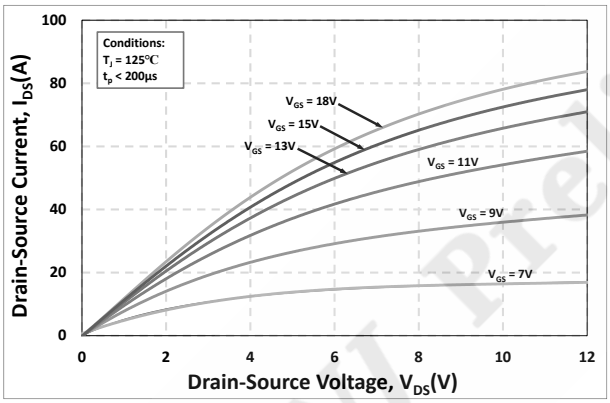


Figure 3. Output Characteristics T_J = 125℃

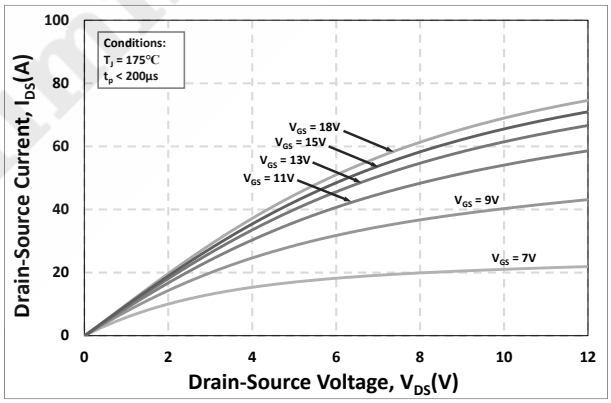


Figure 4. Output Characteristics T_J = 175℃

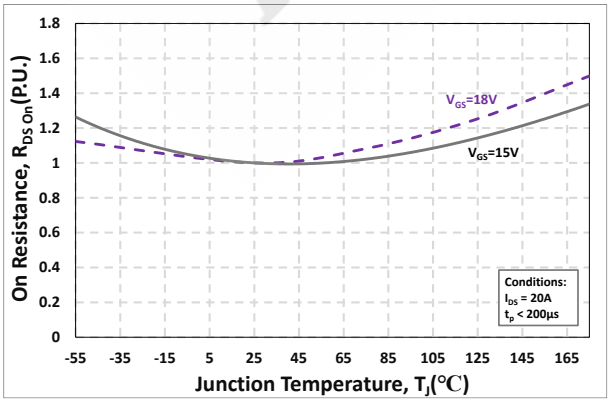


Figure 5. Normalized On-Resistance vs. Temperature

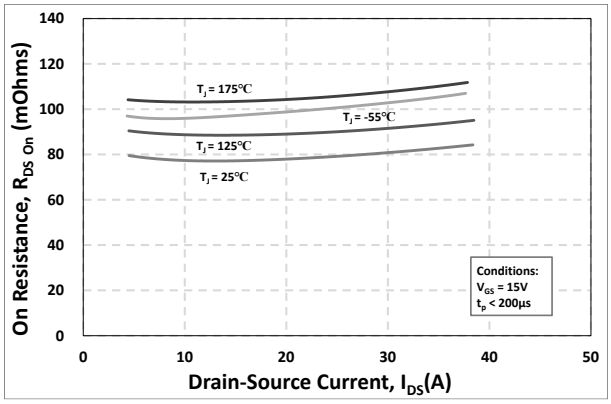


Figure 6. On-Resistance vs. Drain Current Various Temperatures

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.

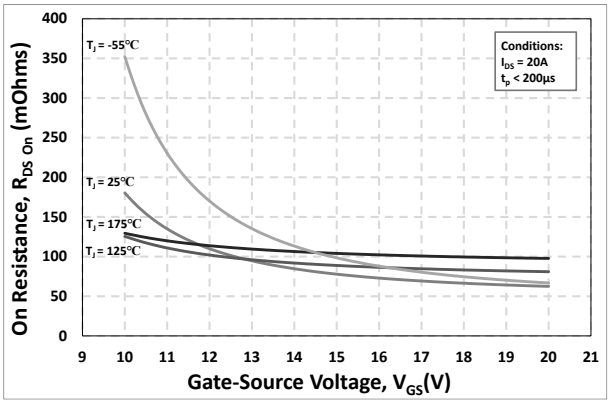


Figure 7. On-Resistance vs. Gate-Source Voltage

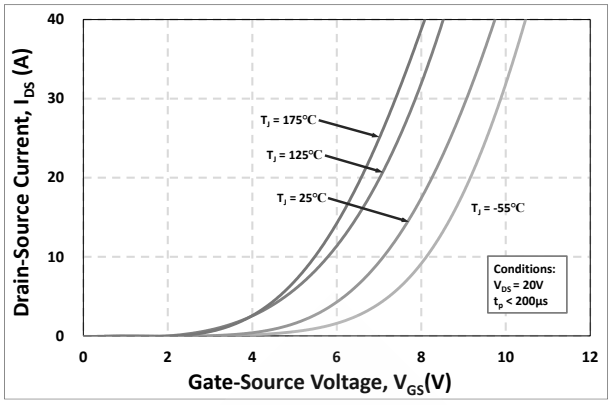


Figure 8. Transfer Characteristic for Various Junction Temperatures

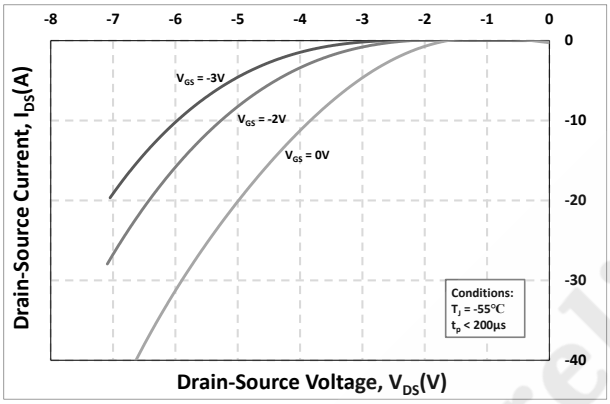


Figure 9. Body Diode Characteristic at -55°C

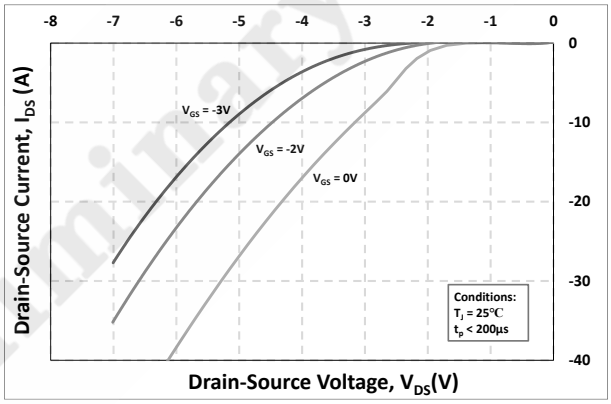


Figure 10. Body Diode Characteristic at 25°C

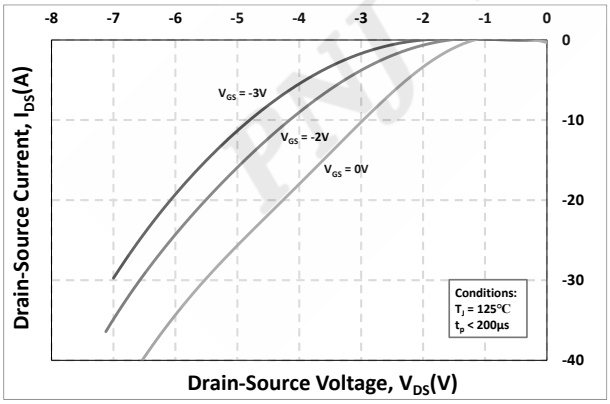


Figure 11. Body Diode Characteristic at 125°C

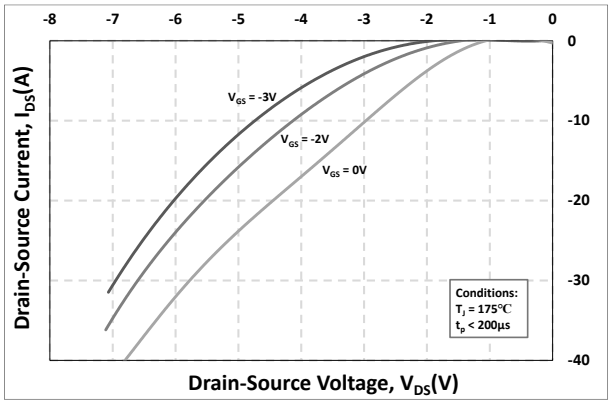


Figure 12. Body Diode Characteristic at 175°C

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.

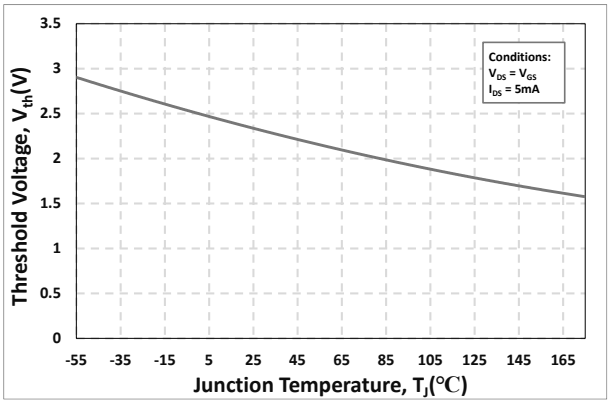


Figure 13. Threshold Voltage vs. Temperature

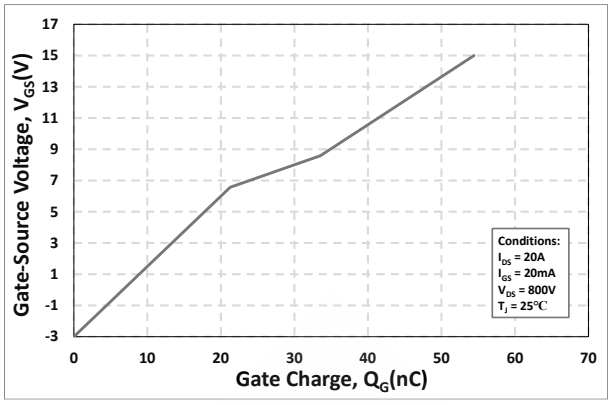


Figure 14. Gate Charge Characteristics

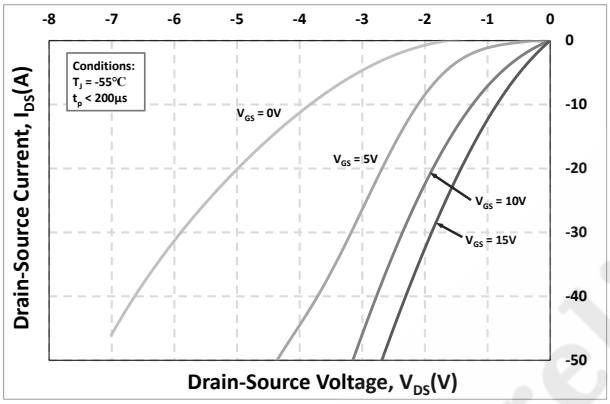


Figure 15. 3rd Quadrant Characteristic at -55°C

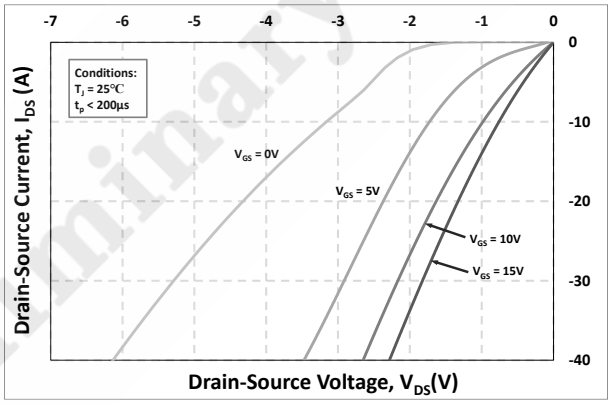


Figure 16. 3rd Quadrant Characteristic at 25°C

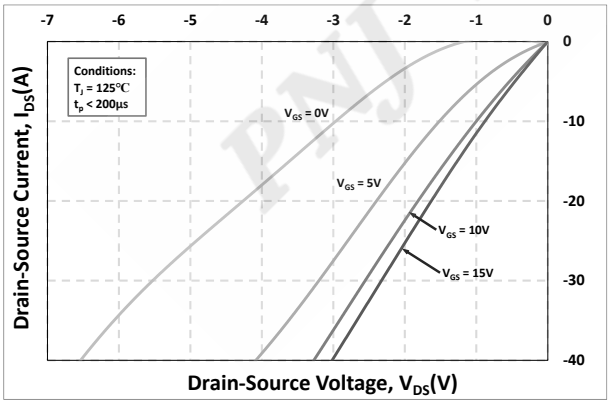


Figure 17. 3rd Quadrant Characteristic at 125°C

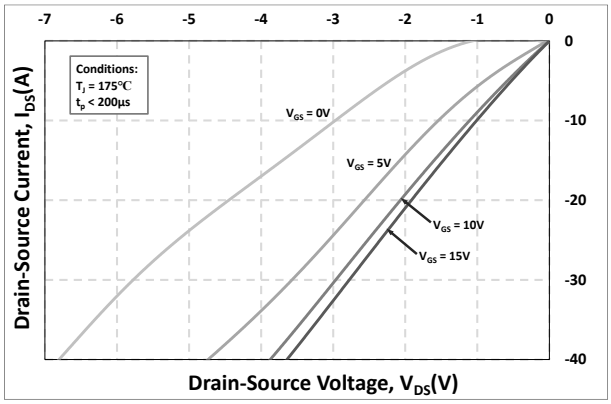


Figure 18. 3rd Quadrant Characteristic at 175°C

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.

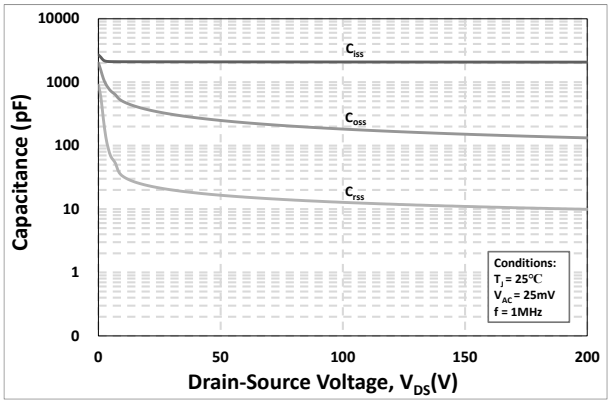


Figure 19. Capacitances vs. Drain-Source Voltage (0 - 200V)

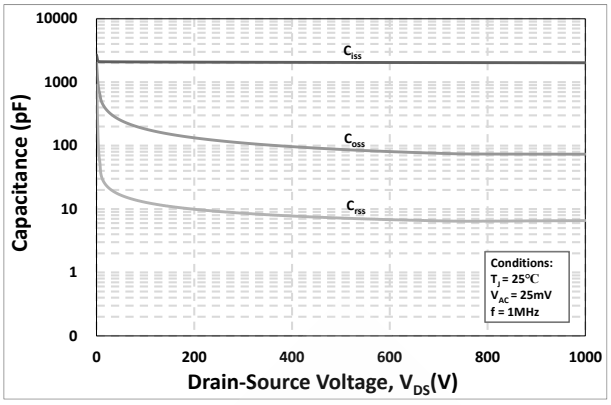


Figure 20. Capacitances vs. Drain-Source Voltage (0 - 1000V)

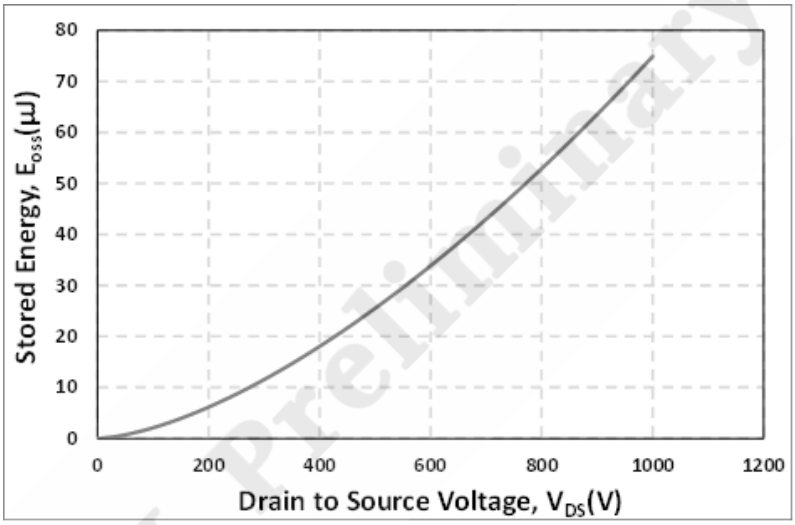
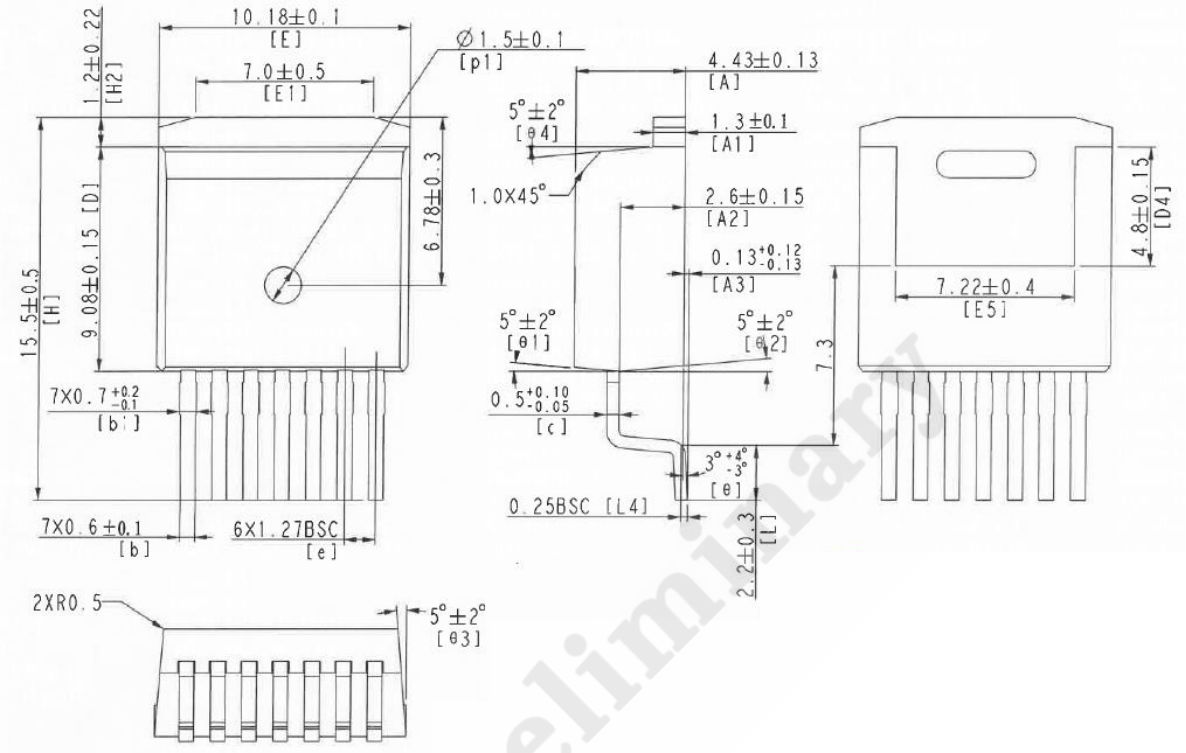


Figure 21. Output Capacitor Stored Energy

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.

6. Package Outlines



Drawing and Dimensions

PNJ Preliminary

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.
■www.pnjsemi.com

Important Notice

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, PN Junction hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

PN Junction reserves the right to make changes at any time to any products or information herein, without notice. “Typical” parameters which may be provided in PN Junction data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including “Typical” must be validated for each customer application by customer’s technical experts.

In addition, any information given in this document is subject to customer’s compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer’s products and any use of the product of PN Junction in customer’s applications. The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer’s technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest PN Junction office (www.pnjsemi.com).

PNJ Preliminary

Warnings

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest PN Junction office.

Except as otherwise explicitly approved by PN Junction in a written document signed by authorized representatives of PN Junction, PN Junction’s products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

Copyright © PN Junction Semiconductor Co., Ltd.
All Rights Reserved.